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[Diodes Incorporated](#)
[DMN313DLT-7](#)

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DMN313DLT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = 25^\circ C$
30V	2Ω @ $V_{GS} = 4V$	270mA
	3.2Ω @ $V_{GS} = 2.5V$	210mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected up to 2kV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)

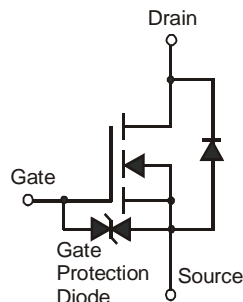
NEW PRODUCT



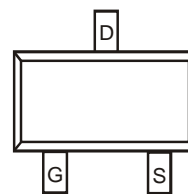
SOT-523



Top View



Equivalent Circuit



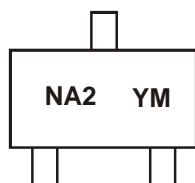
Top View Pin-Out

Ordering Information (Note 3)

Part Number	Case	Packaging
DMN313DLT-7	SOT-523	3000 / Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



NA2 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: X = 2010)
 M = Month (ex: 9 = September)

Date Code Key

Year Code	2010	2011	2012	2013	2014	2015	2016
	X	Y	Z	A	B	C	D

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	1	2	3	4	5	6	7	8	9	O	N	D



DMN313DLT

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 4) V _{GS} = 4.0V	Steady State	T _A = 25°C	I _D	0.27	A
		T _A = 70°C	I _D	0.21	A
Continuous Drain Current (Note 5) V _{GS} = 4.0V	Steady State	T _A = 25°C	I _D	0.31	A
		T _A = 70°C	I _D	0.25	A
Continuous Drain Current (Note 5) V _{GS} = 4.0V	t ≤ 10s	T _A = 25°C	I _D	0.38	A
		T _A = 70°C	I _D	0.3	A
Continuous Drain Current (Note 4) V _{GS} = 2.5V	Steady State	T _A = 25°C	I _D	0.21	A
		T _A = 70°C	I _D	0.15	A
Continuous Drain Current (Note 5) V _{GS} = 2.5V	t ≤ 10s	T _A = 25°C	I _D	0.29	A
		T _A = 70°C	I _D	0.22	A
Pulsed Drain Current (Note 6)			I _{DM}	1.2	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P _D	0.28	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	R _{θJA}	474	°C/W
Power Dissipation (Note 5)	P _D	0.36	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5)	R _{θJA}	361	°C/W
Power Dissipation (Note 5) t ≤ 10s	P _D	0.52	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5) t ≤ 10s	R _{θJA}	252	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	0.1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	1.3	2	Ω	V _{GS} = 4V, I _D = 10mA
		-	1.6	3.2		V _{GS} = 2.5V, I _D = 1mA
Forward Transfer Admittance	Y _{fs}	-	93	-	mS	V _{DS} = 3V, I _D = 10mA
Diode Forward Voltage	V _{SD}	-	0.7	1.3	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	36.3	-	pF	V _{DS} = 5V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	7.6	-		
Reverse Transfer Capacitance	C _{rss}	-	4.7	-		
Gate Resistance	R _g	-	128	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	0.5	-	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 10mA
Gate-Source Charge	Q _{gs}	-	0.1	-		
Gate-Drain Charge	Q _{gd}	-	0.1	-		
Turn-On Delay Time	t _{D(on)}	-	4.5	-	ns	V _{GS} = 4.5V, V _{DS} = 15V, R _G = 2Ω, I _D = 180mA
Turn-On Rise Time	t _r	-	2.24	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	19.2	-	ns	
Turn-Off Fall Time	t _f	-	28.2	-	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



DMN313DLT

NEW PRODUCT

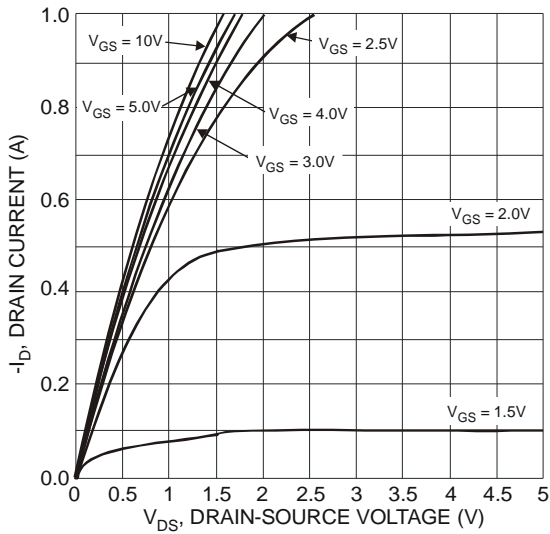


Fig. 1 Typical Output Characteristics

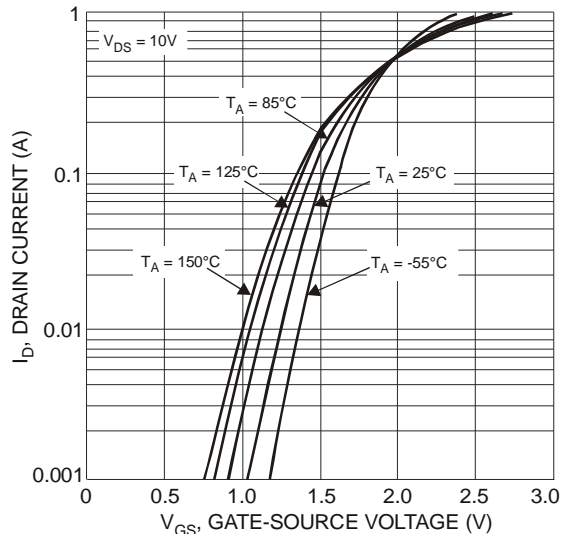


Fig. 2 Typical Transfer Characteristics

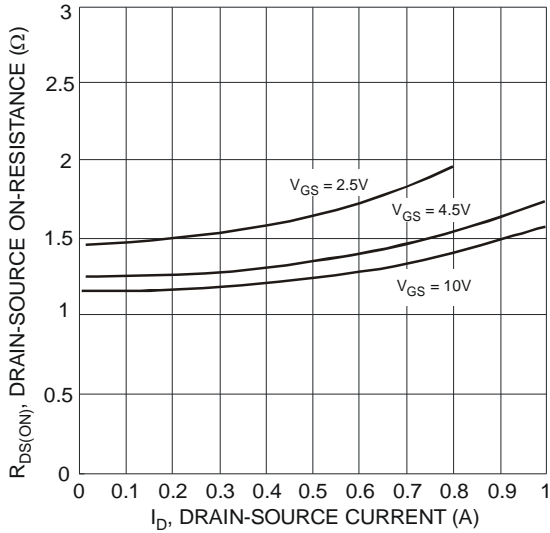


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

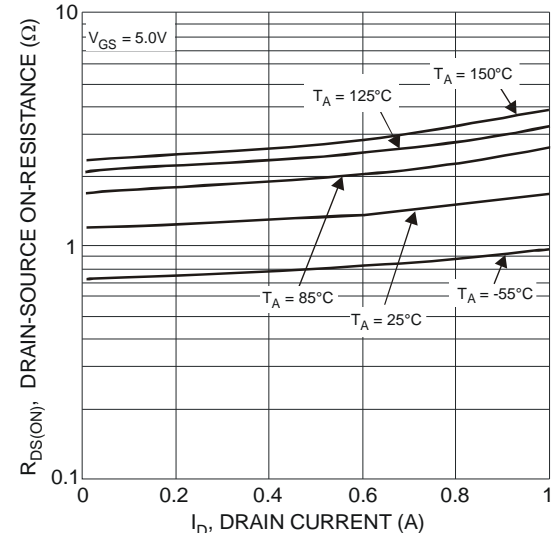


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

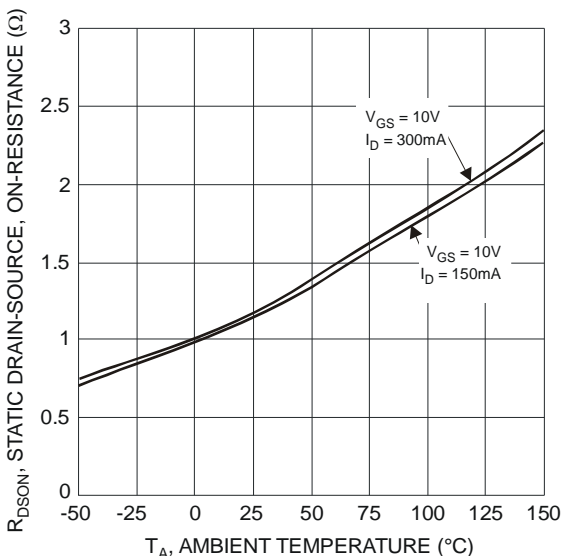


Fig. 5 On-Resistance Variation with Temperature

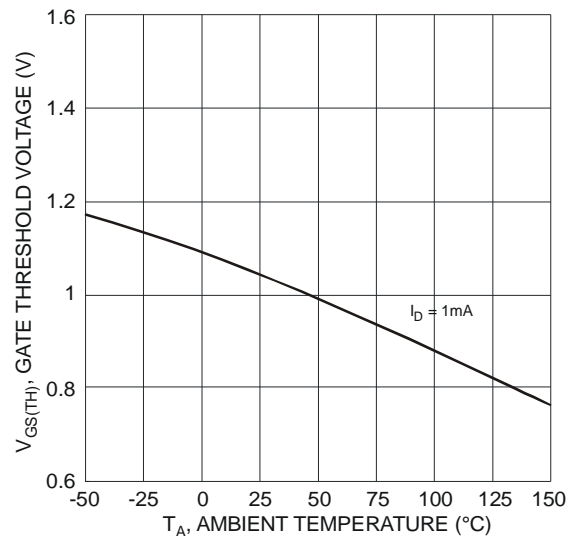


Fig. 6 Gate Threshold Variation vs. Ambient Temperature



DMN313DLT

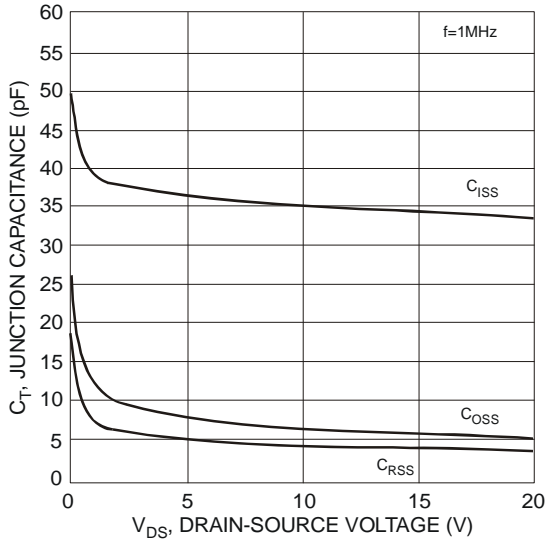


Fig. 7 Typical Junction Capacitance

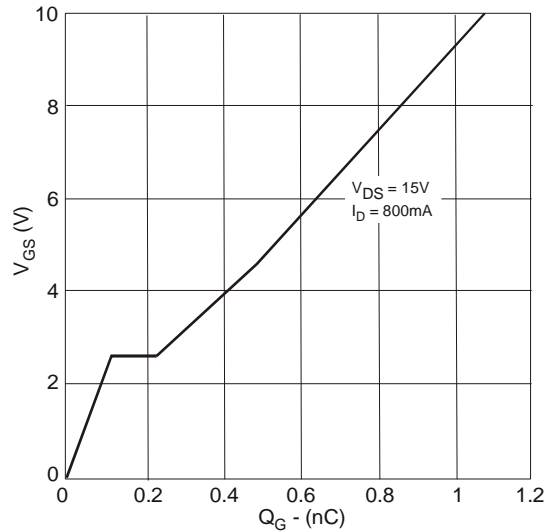


Fig. 08 Gate Charge Characteristics

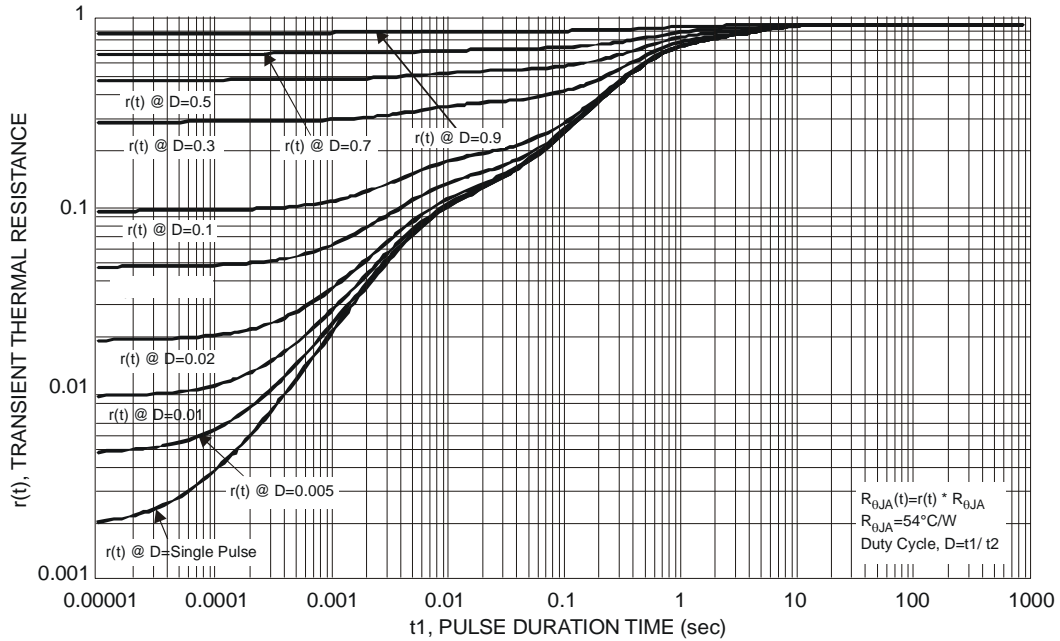
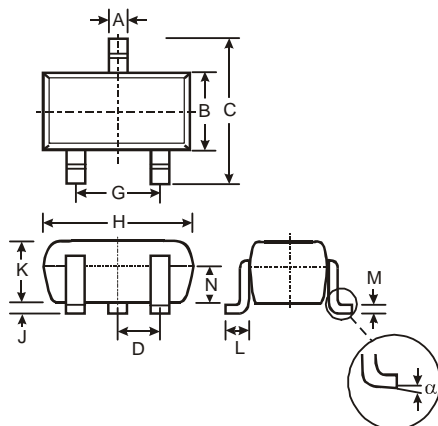


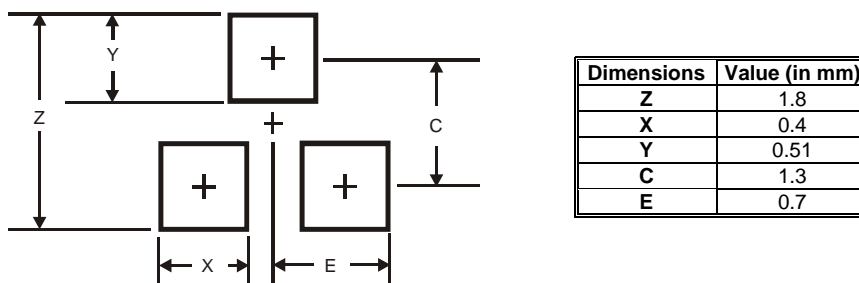
Fig. 9 Transient Thermal Resistance

Package Outline Dimensions



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



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